20V Half Bridge Dual N-Channel Super Trench Power MOSFET

Description

The HM30SDN02D uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g. It includes two specialized MOSFETs in a dual Power DFN5x6 package.

General Features

Q1 "High Side" MOSFET **Q2 "Low Side" MOSFET**

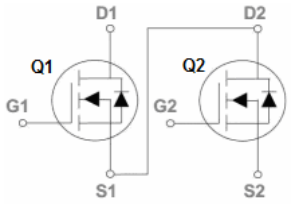
- V_{DS} =20V,I_D =30A V_{DS} =20V,I_D =30A
  $R_{DS(ON)}$ <8mΩ @ V_{GS}=10V $R_{DS(ON)}$ <8mΩ @ V_{GS}=10V
  $R_{DS(ON)}$<8.5mΩ @ V_{GS}=4.5V $R_{DS(ON)}$ <8.5mΩ @ V_{GS}=4.5V
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 150 °C operating temperature
- Pb free terminal plating
- RoHS compliant
- Halogen free

Application

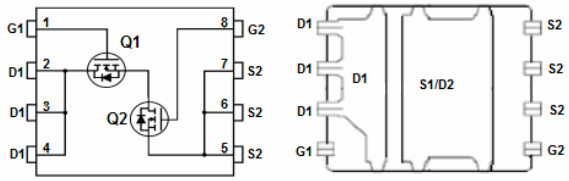
- Compact DC/DC converter applications

100% UIS TESTED!

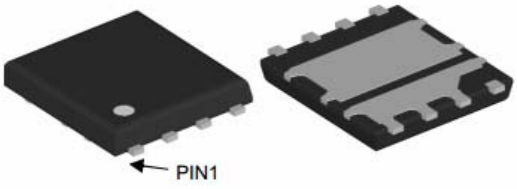
100% ΔVds TESTED!



Schematic Diagram



pin assignment



Top View **Bottom View**

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HM30SDN02D	HM30SDN02D	DFN5X6-8L	330mm	12mm	5000 units

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter		Symbol	Q1	Q2	Unit
Drain-Source Voltage		V_{DS}	20	20	V
Gate-Source Voltage		V_{GS}	±20	±20	V
Drain Current-Continuous (Note 2)	T_C=25°C	I_D	30	30	A
	T_C=100°C		21	21	A
Drain Current -Pulsed (Note 1)		I_{DM}	90	90	
Power Dissipation	T_C=25°C	P_D	30	80	W
Operating Junction and Storage Temperature Range		T_J,T_{STG}	-55 To 150	-55 To 150	℃

Thermal Characteristic

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance,Junction-to-Case (Note 2) **(Q1)**	$R_{\theta JC}$	3.3	4.2	℃/W
Thermal Resistance,Junction-to-Case (Note 2) **(Q2)**	$R_{\theta JC}$	1.2	1.6	℃/W

Q1 Electrical Characteristics (T_C=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	20		-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=20V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	0.4		1.2	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=15A	-	5.0	8.0	mΩ
		V_{GS}=4.5V, I_D=15A	-	5.5	8.5	mΩ
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=15A		30	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=15V,V_{GS}=0V, F=1.0MHz	-	822	-	PF
Output Capacitance	C_{oss}		-	344	-	PF
Reverse Transfer Capacitance	C_{rss}		-	15.3	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=15V,I_D=15A V_{GS}=10V,R_G=1.6Ω	-	6.5	-	nS
Turn-on Rise Time	t_r		-	2.5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	17	-	nS
Turn-Off Fall Time	t_f		-	2.5	-	nS
Total Gate Charge	Q_g	V_{DS}=15V,I_D=15A, V_{GS}=10V	-	15	-	nC
Gate-Source Charge	Q_{gs}		-	2.9		nC
Gate-Drain Charge	Q_{gd}		-	2.1		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=20A	-		1.2	V
Diode Forward Current (Note 2)	I_S		-	-	30	A
Reverse Recovery Time	t_{rr}	T_J = 25°C, I_F = I_S di/dt = 100A/μs (Note3)	-	11	-	nS
Reverse Recovery Charge	Qrr		-	19	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition : Tj=25℃,V_{DD}=15V,V_G=10V,L=0.5mH,Rg=25Ω

Q1Typical Electrical and Thermal Characteristics

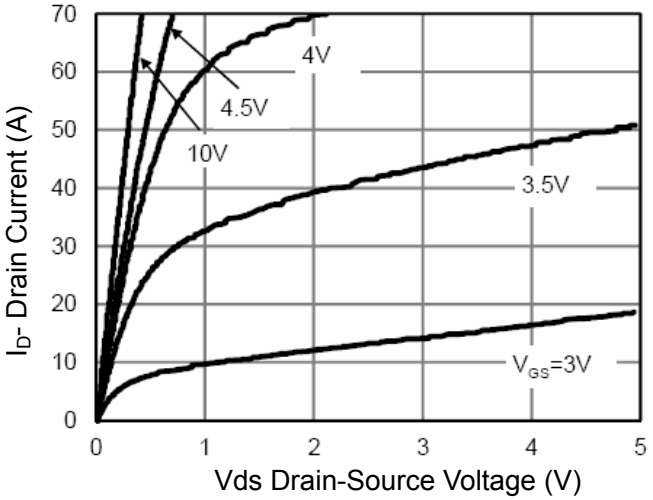


Figure 1 Output Characteristics

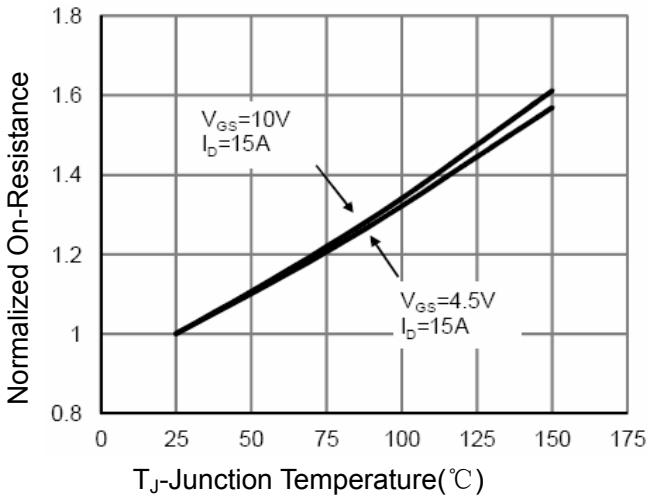


Figure 4 Rdson-Junction Temperature

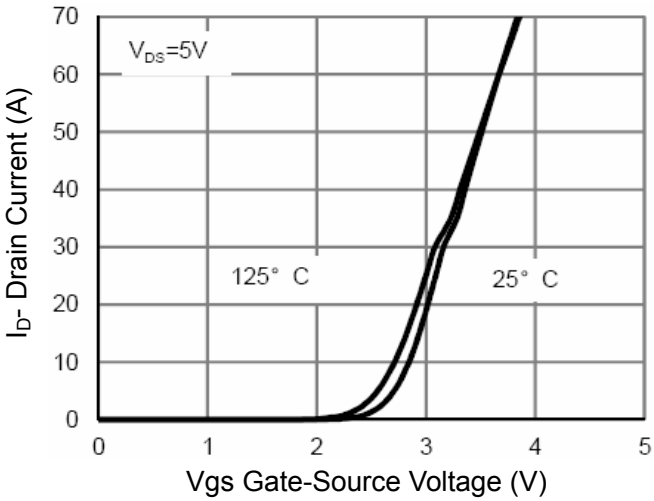


Figure 2 Transfer Characteristics

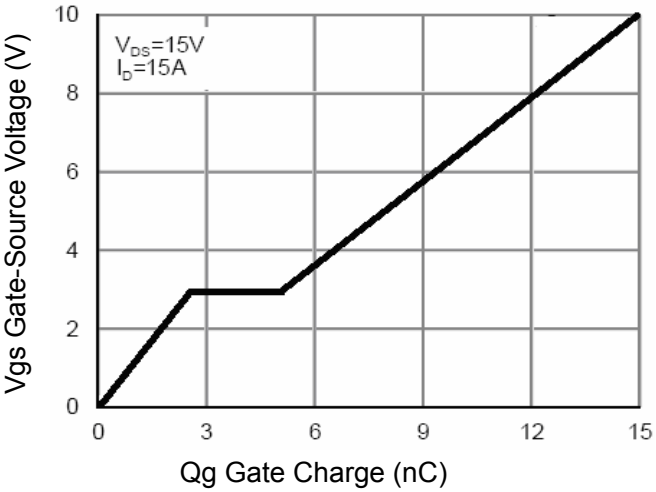


Figure 5 Gate Charge

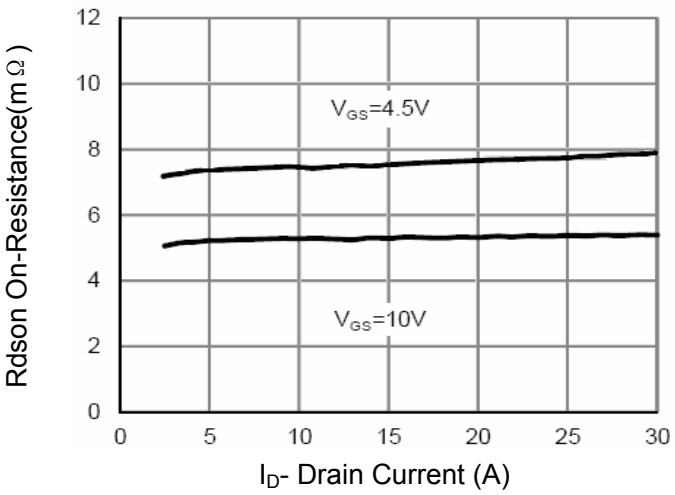


Figure 3 Rdson- Drain Current

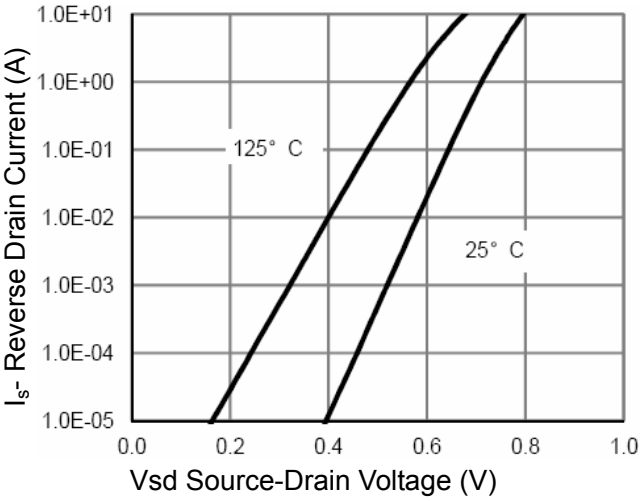


Figure 6 Source- Drain Diode Forward

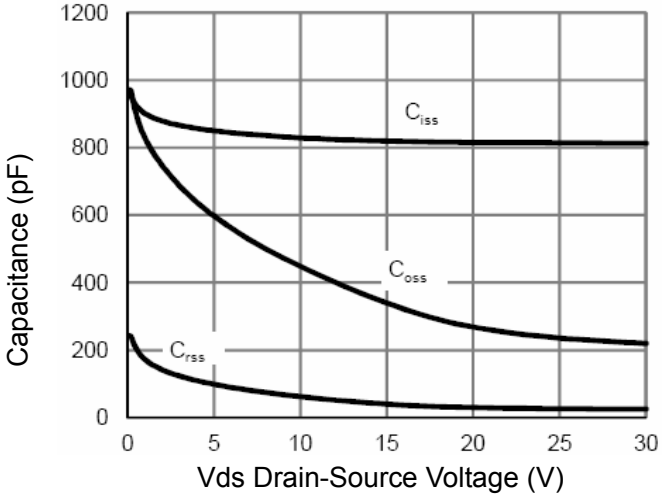


Figure 7 Capacitance vs Vds

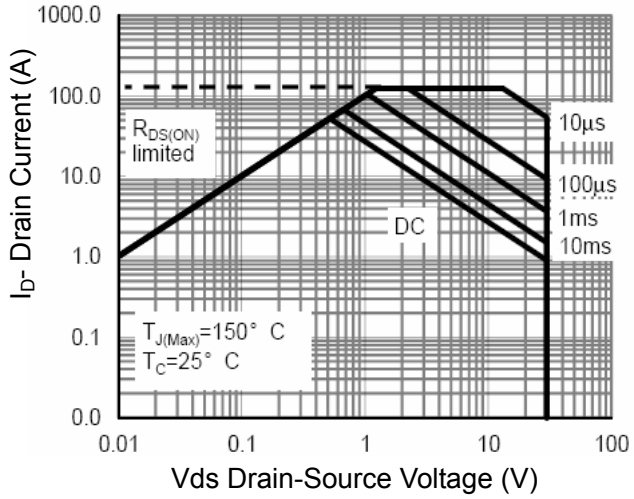


Figure 8 Safe Operation Area

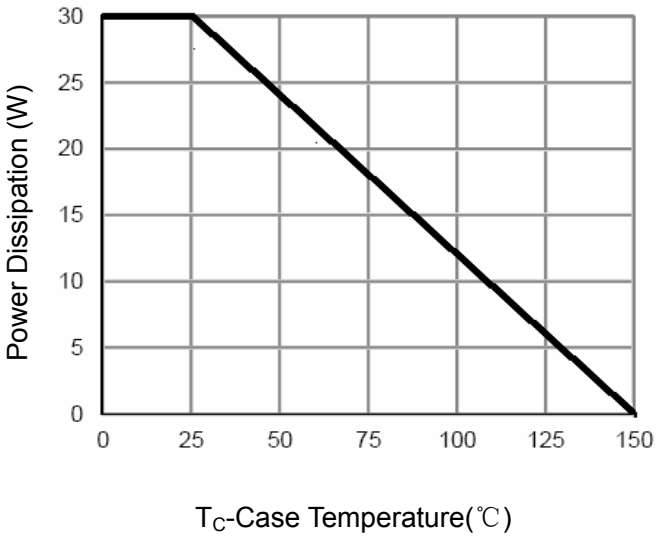


Figure 9 Power De-rating

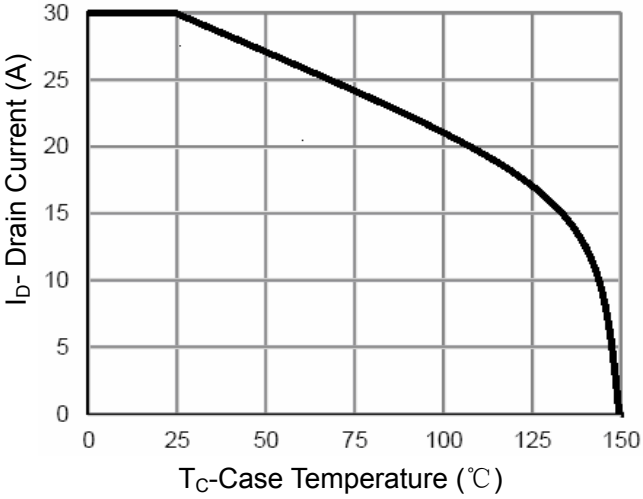


Figure 10 Current De-rating

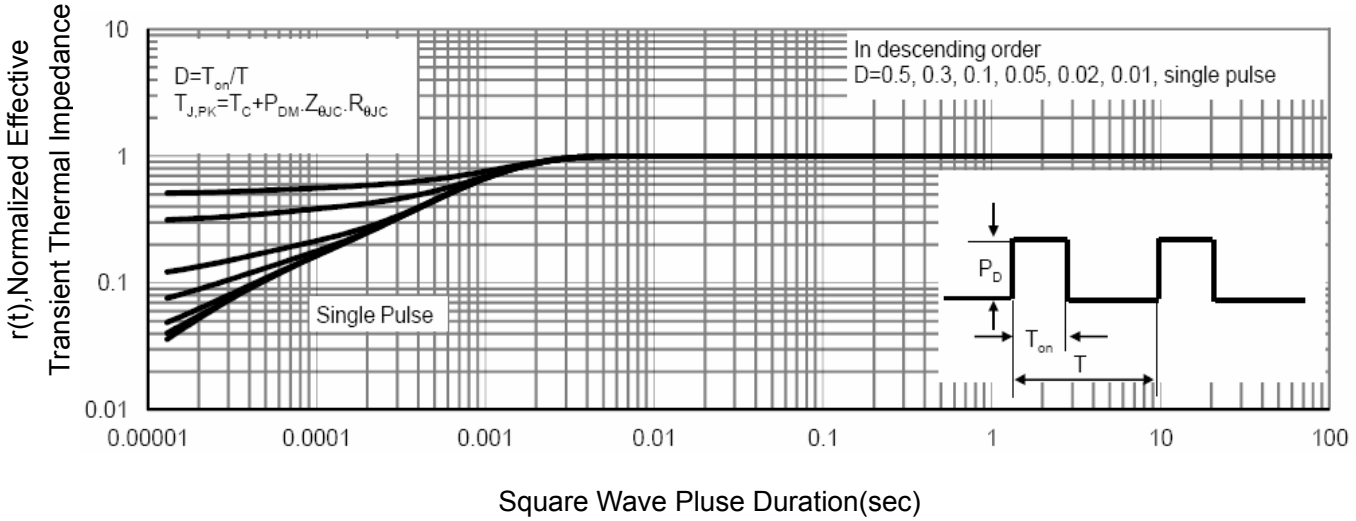


Figure 11 Normalized Maximum Transient Thermal Impedance

Q2 Electrical Characteristics (TC=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	20		-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=20V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±10	μA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	0.4		1.2	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=50A	-	5.0	8.0	mΩ
		V_{GS}=4.5V, I_D=50A	-	5.5	8.5	mΩ
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=50A		65	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=15V,V_{GS}=0V, F=1.0MHz	-	3370	-	PF
Output Capacitance	C_{oss}		-	902	-	PF
Reverse Transfer Capacitance	C_{rss}		-	60	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=15V,I_D=50A V_{GS}=10V,R_G=1.6Ω	-	7	-	nS
Turn-on Rise Time	t_r		-	5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	32	-	nS
Turn-Off Fall Time	t_f		-	9	-	nS
Total Gate Charge	Q_g	V_{DS}=15V,I_D=50A, V_{GS}=10V	-	55	-	nC
Gate-Source Charge	Q_{gs}		-	9		nC
Gate-Drain Charge	Q_{gd}		-	8.5		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=50A	-		1.2	V
Diode Forward Current (Note 2)	I_S		-	-	30	A
Reverse Recovery Time	t_{rr}	T_J = 25°C, I_F = I_S di/dt = 500A/μs (Note3)	-	20	-	nS
Reverse Recovery Charge	Qrr		-	50	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition : Tj=25℃,V_{DD}=15V,V_G=10V,L=0.5mH,Rg=25Ω

Q2 Typical Electrical and Thermal Characteristics

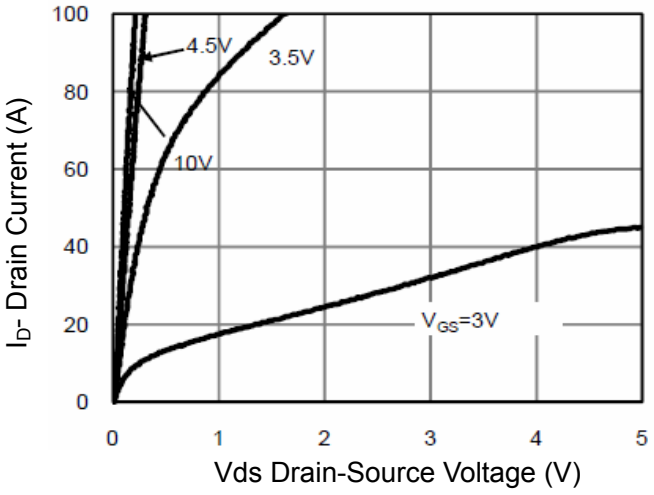


Figure 1 Output Characteristics

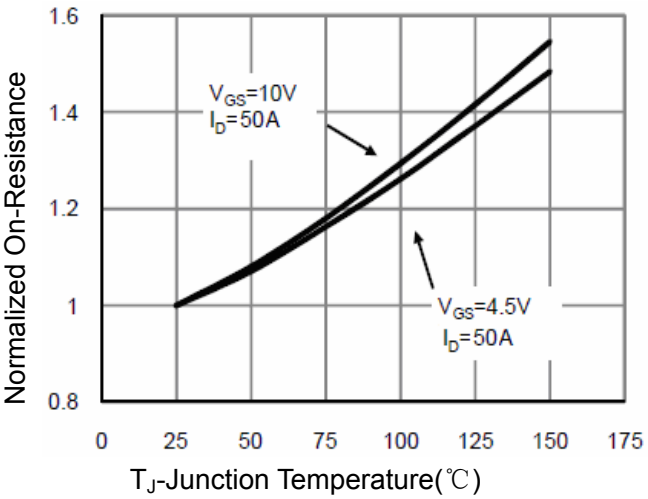


Figure 4 Rdson-Junction Temperature

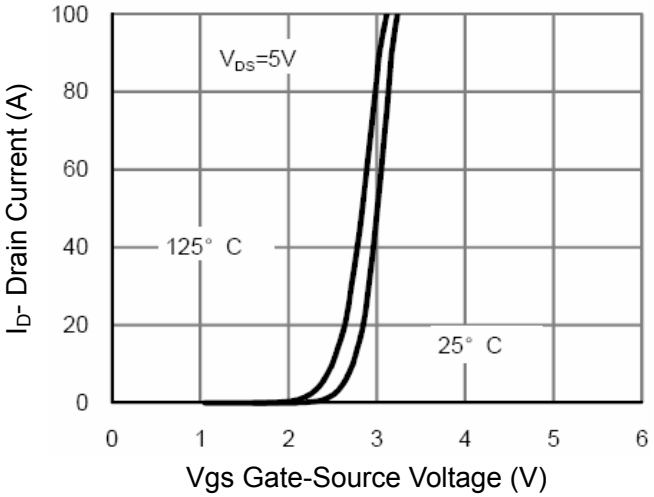


Figure 2 Transfer Characteristics

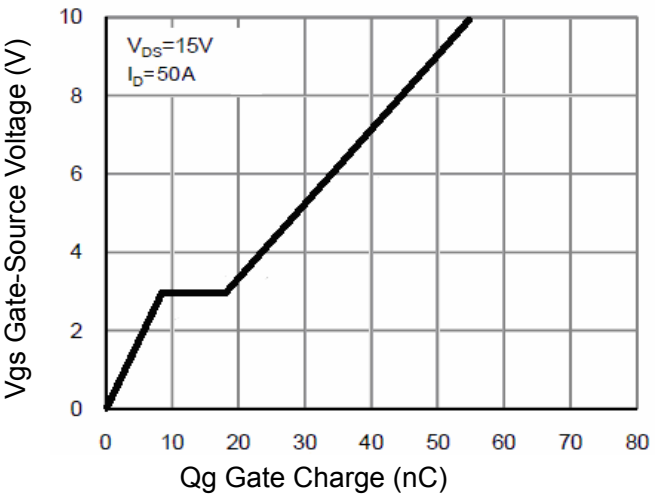


Figure 5 Gate Charge

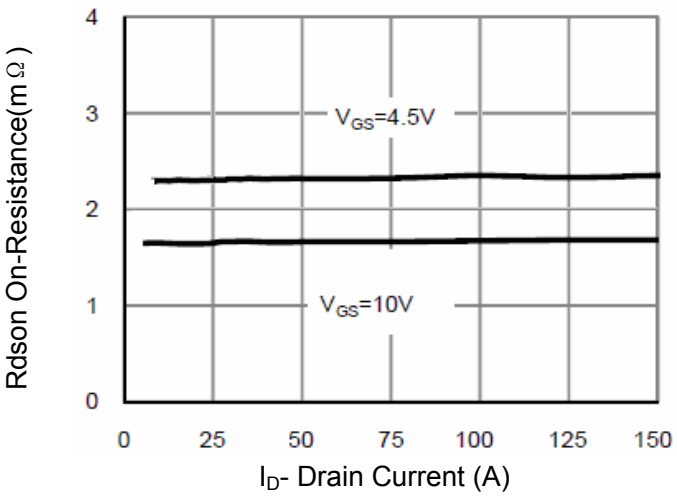


Figure 3 Rdson- Drain Current

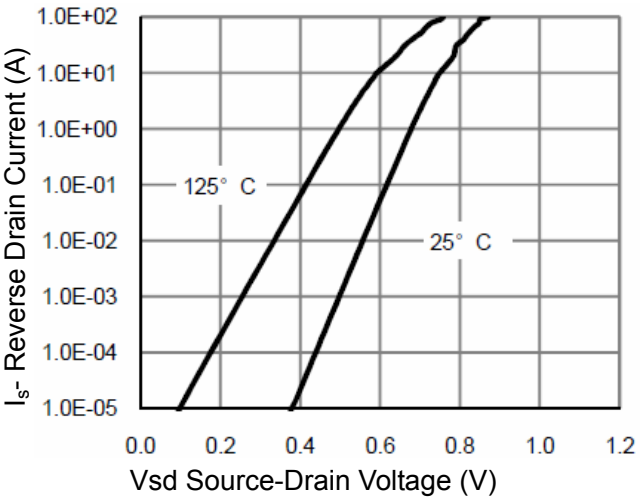


Figure 6 Source- Drain Diode Forward

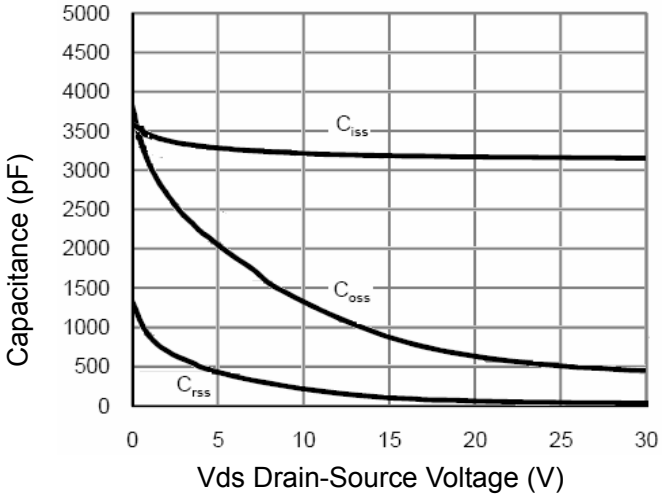


Figure 7 Capacitance vs Vds

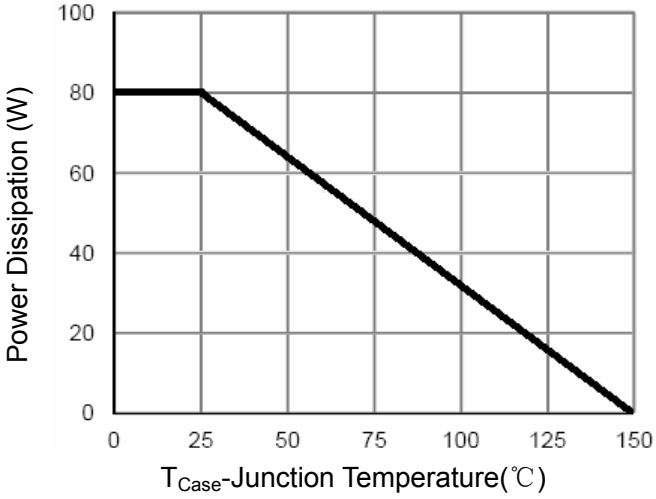


Figure 9 Power De-rating

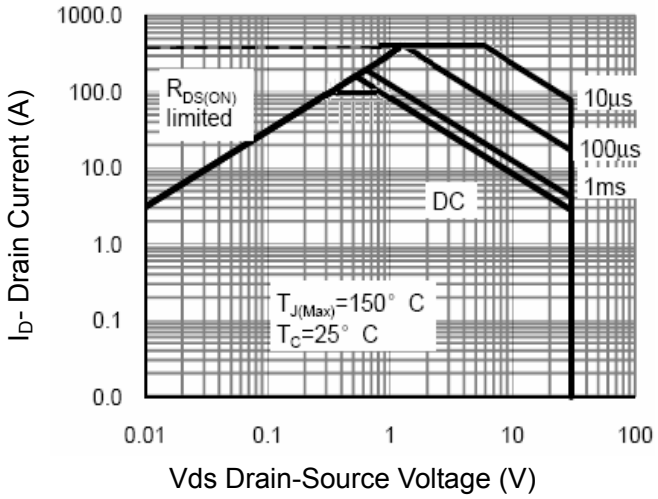


Figure 8 Safe Operation Area

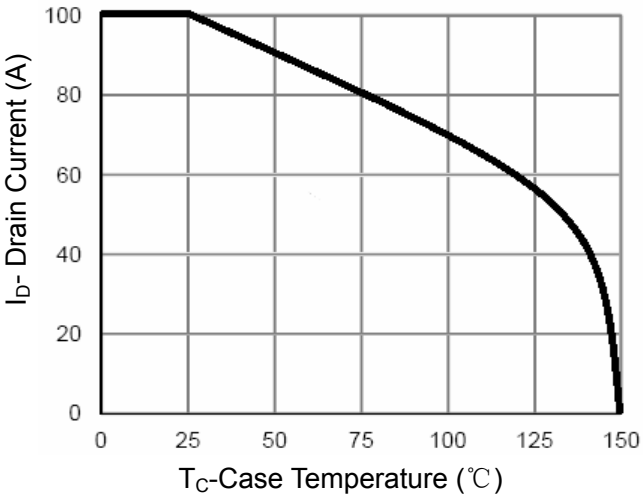


Figure 10 Current De-rating

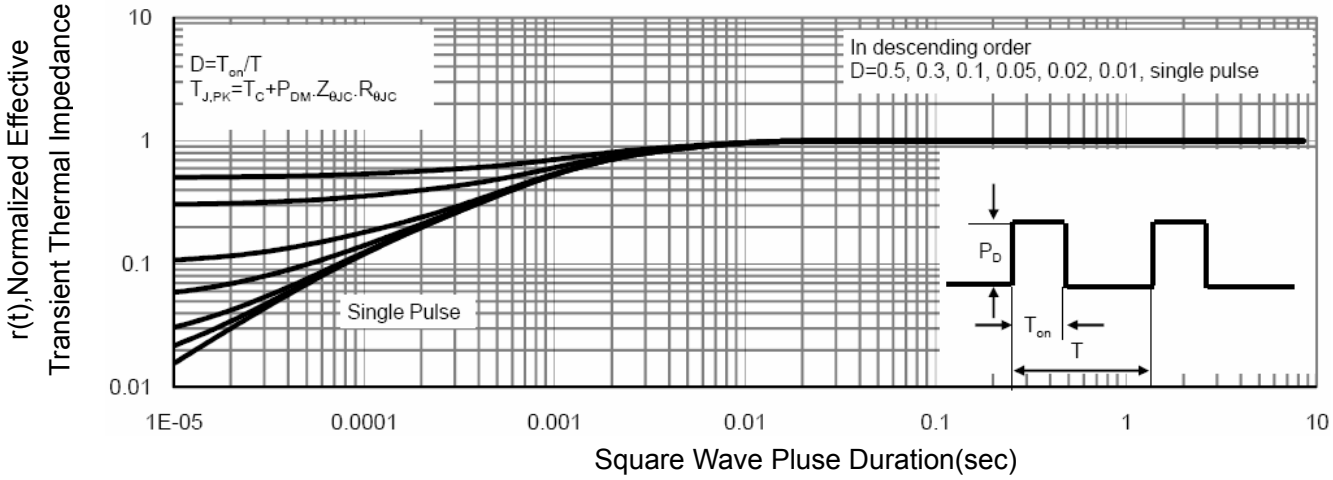
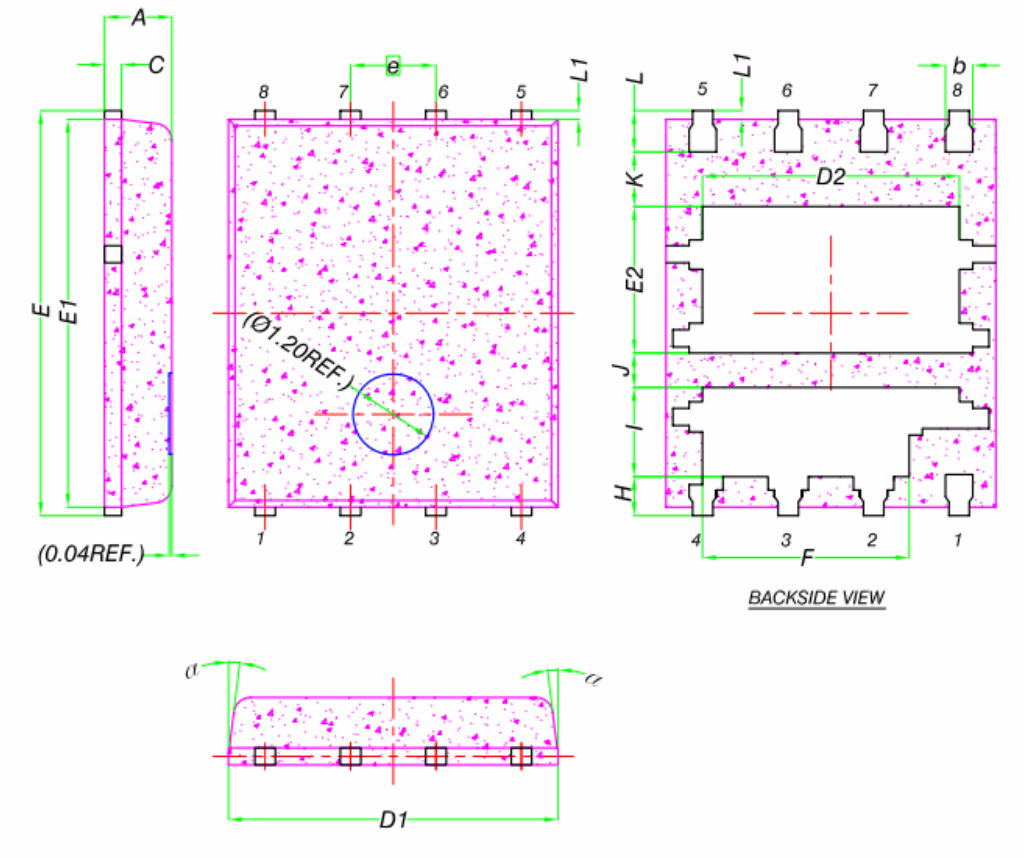
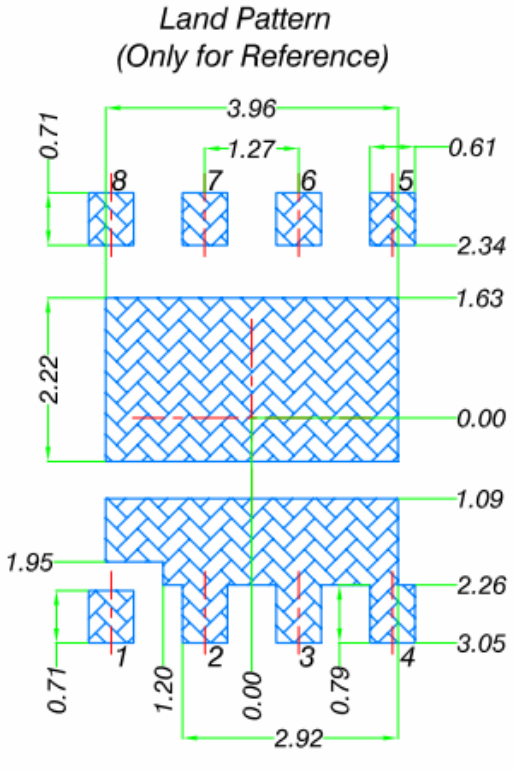


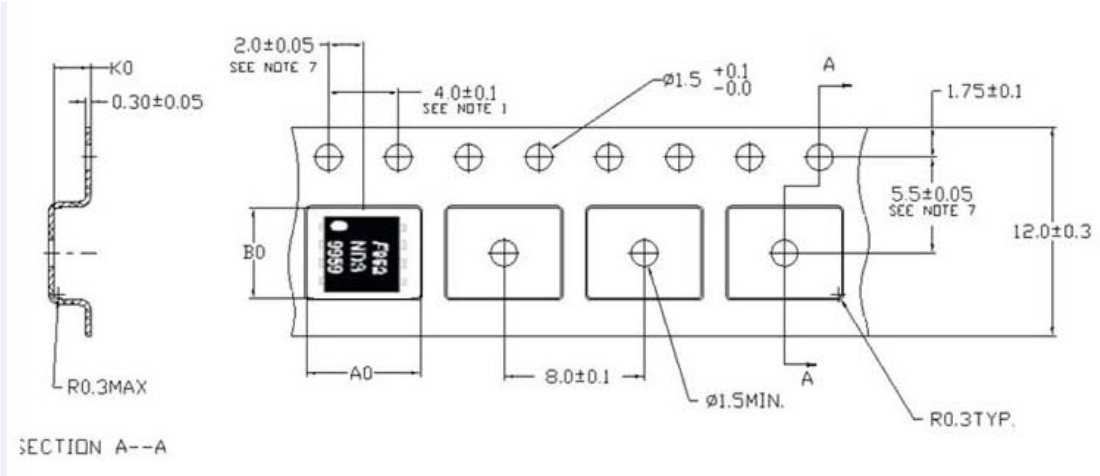
Figure 11 Normalized Maximum Transient Thermal Impedance

DFN5X6-8L Package Information



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	2.02	2.17	2.32
e	1.27 BSC		
F	2.87	3.07	3.22
H	0.48	0.58	0.68
I	1.22	1.32	1.42
J	0.40	0.50	0.60
K	0.50	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
α	0°	-	12°




K0
0.30±0.05
R0.3MAX
SECTION A--A
2.0±0.05
SEE NOTE 7
4.0±0.1
SEE NOTE 1
ø1.5 +0.1 -0.0
A
1.75±0.1
5.5±0.05
SEE NOTE 7
12.0±0.3
B0
A0
8.0±0.1
ø1.5MIN.
R0.3TYP.